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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 15x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302r8t6

3.4 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.5 Power management

3.5.1 Power supply schemes

- V_{SS}, V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. It is provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supply for ADC, DAC, comparators, operational amplifier, reset blocks, RCs and PLL. The minimum voltage to be applied to V_{DDA} differs from one analog peripheral to another. *Table 2* provides the summary of the V_{DDA} ranges for analog peripherals. The V_{DDA} voltage level must always be greater than or equal to the V_{DD} voltage level and must be provided first.

Table 2. External analog supply values for analog peripherals

Analog peripheral	Minimum V_{DDA} supply	Maximum V_{DDA} supply
ADC/COMP	2.0 V	3.6 V
DAC/OPAMP	2.4 V	3.6 V

- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.5.2 Power supply supervisor

The device has an integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device remains in reset mode when the monitored supply voltage is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.18 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32F302x6/8 devices have three embedded universal synchronous receiver transmitters (USART1, USART2 and USART3).

The USART interfaces are able to communicate at speeds of up to 9 Mbit/s.

All USARTs support hardware management of the CTS and RTS signals, multiprocessor communication mode, single-wire half-duplex communication mode and synchronous mode.

USART1 supports SmartCard mode, IrDA SIR ENDEC, LIN Master capability and autobaudrate detection.

All USART interfaces can be served by the DMA controller.

Refer to *Table 7* for the features available in all USARTs interfaces.

Table 7. USART features

USART modes/features(1)	USART1	USART2	USART3
Hardware flow control for modem	X	X	X
Continuous communication using DMA	X	X	X
Multiprocessor communication	X	X	X
Synchronous mode	X	X	X
SmartCard mode	X	-	-
Single-wire half-duplex communication	X	X	X
IrDA SIR ENDEC block	X	-	-
LIN mode	X	-	-
Dual clock domain and wakeup from Stop mode	X	-	-
Receiver timeout interrupt	X	-	-
Modbus communication	X	-	-
Auto baud rate detection	X	-	-
Driver Enable	X	X	X

1. X = supported.

3.19 Serial peripheral interfaces (SPI)/Inter-integrated sound interfaces (I2S)

Two SPI interfaces (SPI2 and SPI3) allow communication up to 18 Mbit/s in slave and master modes in full-duplex and simplex modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available, that can be operated in master or slave mode. These interfaces can be configured to operate with 16/32 bit resolution, as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master

mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

Refer to *Table 8* for the features available in SPI2 and SPI3.

Table 8. STM32F302x6/8 SPI/I2S implementation

SPI features(1)	SPI2	SPI3
Hardware CRC calculation	X	X
Rx/Tx FIFO	X	X
NSS pulse mode	X	X
I2S mode	X	X
TI mode	X	X

1. X = supported.

3.20 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.21 Universal serial bus (USB)

The STM32F302x6 STM32F302x8 embeds a full-speed USB device peripheral compliant with the USB specification version 2.0. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up-to 1 KB (the last 256 bytes are used for CAN peripheral if enabled) and suspend/resume support. It requires a precise 48 MHz clock which is generated from the internal main PLL (the clock source must use an HSE crystal oscillator).

3.22 Touch sensing controller (TSC)

The STM32F302x6/8 devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 18 capacitive sensing channels distributed over 6 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (for example glass, plastic). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

Table 9. Capacitive sensing GPIOs available on STM32F302x6/8 devices

Group	Capacitive sensing signal name	Pin name
1	TSC_G1_IO1	PA0
	TSC_G1_IO2	PA1
	TSC_G1_IO3	PA2
	TSC_G1_IO4	PA3
2	TSC_G2_IO1	PA4
	TSC_G2_IO2	PA5
	TSC_G2_IO3	PA6
	TSC_G2_IO4	PA7
3	TSC_G3_IO1	PC5
	TSC_G3_IO2	PB0
	TSC_G3_IO3	PB1
	TSC_G3_IO4	PB2
4	TSC_G4_IO1	PA9
	TSC_G4_IO2	PA10
	TSC_G4_IO3	PA13
	TSC_G4_IO4	PA14
5	TSC_G5_IO1	PB3
	TSC_G5_IO2	PB4
	TSC_G5_IO3	PB6
	TSC_G5_IO4	PB7
6	TSC_G6_IO1	PB11
	TSC_G6_IO2	PB12
	TSC_G6_IO3	PB13
	TSC_G6_IO4	PB14

Table 10. No. of capacitive sensing channels available on STM32F302x6/8 devices

Analog I/O group	Number of capacitive sensing channels		
	STM32F302Rx	STM32F302Cx	STM32F302Kx
G1	3	3	3
G2	3	3	3
G3	3	2	1
G4	3	3	3
G5	3	3	3

Table 12. STM32F302x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	-	-	51	PC10	I/O	FT	-	EVENTOUT, SPI3_SCK/I2S3_CK, USART3_TX	-
-	-	-	52	PC11	I/O	FT	-	EVENTOUT, SPI3_MISO/I2S3ext_SD, USART3_RX	-
-	-	-	53	PC12	I/O	FT	-	EVENTOUT, SPI3_MOSI/I2S3_SD, USART3_CK	-
-	-	-	54	PD2	I/O	FT	-	EVENTOUT	-
26	A3	39	55	PB3	I/O	FT	-	JTDO-TRACESWO, TIM2_CH2, TSC_G5_IO1, SPI3_SCK/I2S3_CK, USART2_TX, EVENTOUT	-
27	A4	40	56	PB4	I/O	FT	-	JTRST, TIM16_CH1, TSC_G5_IO2, SPI3_MISO/I2S3ext_SD, USART2_RX, TIM17_BKIN, EVENTOUT	-
28	B4	41	57	PB5	I/O	FT	-	TIM16_BKIN, I2C1_SMBAI, SPI3_MOSI/I2S3_SD, USART2_CK, I2C3_SDA, TIM17_CH1, EVENTOUT	-
29	C4	42	58	PB6	I/O	FTf	-	TIM16_CH1N, TSC_G5_IO3, I2C1_SCL, USART1_TX, EVENTOUT	-
30	D4	43	59	PB7	I/O	FTf	-	TIM17_CH1N, TSC_G5_IO4, I2C1_SDA, USART1_RX, EVENTOUT	-

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 19: Voltage characteristics*, *Table 20: Current characteristics*, and *Table 21: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 19. Voltage characteristics(1)

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage (including V_{DDA}, V_{BAT} and V_{DD})	-0.3	4.0	V
V_{DD}–V_{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V_{IN}(2)	Input voltage on FT and FTf pins	V_{SS} −0.3	V_{DD} + 4.0	V
	Input voltage on TTa and TT pins	V_{SS} −0.3	4.0	
	Input voltage on any other pin	V_{SS} −0.3	4.0	
	Input voltage on Boot0 pin	0	9	
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DD} power pins	-	50	mV
$\lvert V_{SSX} - V_{SS}\rvert$	Variations between all the different ground pins(3)	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.12: Electrical sensitivity characteristics*		V

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range. The following relationship must be respected between V_{DDA} and V_{DD}:
V_{DDA} must power on before or at the same time as V_{DD} in the power up sequence.
V_{DDA} must be greater than or equal to V_{DD}.
2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. Include V_{REF-} pin.

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 23* are derived from tests performed under the ambient temperature condition summarized in *Table 22*.

Table 23. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 24* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{POR/PDR}$(1)	Power on/power down reset threshold	Falling edge	1.8(2)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}$(3)	POR reset temporization	-	1.5	2.5	4.5	ms

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
3. Based on characterization, not tested in production.

Table 31. Typical and maximum V_{DDA} consumption in Stop and Standby modes

Symbol	Parameter	Conditions		Typ @V_{DD} (V_{DD} = V_{DDA})						Max(1)			Unit
				2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DDA}	Supply current in Stop mode	V_{DDA} supervisor ON	Regulator in run/low-power mode, all oscillators OFF	1.70	1.83	1.95	2.08	2.22	2.37	3.40	5.30	5.5	µA
	Supply current in Standby mode		LSI ON and IWDG ON	2.08	2.25	2.41	2.59	2.79	3.01	-	-	-	
			LSI OFF and IWDG OFF	1.59	1.72	1.83	1.96	2.10	2.25	2.80	2.90	3.60	
	Supply current in Stop mode	V_{DDA} supervisor OFF	Regulator in run/low-power mode, all oscillators OFF	0.99	1.01	1.04	1.09	1.14	1.21	-	-	-	
	Supply current in Standby mode		LSI ON and IWDG ON	1.36	1.43	1.50	1.60	1.72	1.85	-	-	-	
			LSI OFF and IWDG OFF	0.87	0.89	0.92	0.97	1.02	1.09	-	-	-	

1. Guaranteed by characterization results.

Table 32. Typical and maximum current consumption from V_{BAT} supply

Symbol	Para meter	Conditions (1)	Typ.@V_{BAT}								Max. @V_{BAT}= 3.6V(2) T_A (°C)			Unit
			1.65V	1.8V	2V	2.4V	2.7V	3V	3.3V	3.6V	25	85	105	
I_{DD_VBAT}	Backup domain supply current	LSE & RTC ON; “Xtal mode” lower driving capability; LSEDRV[1:0] = '00'	0.41	0.43	0.46	0.54	0.59	0.66	0.74	0.82	-	-	-	µA
		LSE & RTC ON; “Xtal mode” higher driving capability; LSEDRV[1:0] = '11'	0.65	0.68	0.73	0.80	0.87	0.95	1.03	1.14	-	-	-	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a CL of 6 pF for typical values.
2. Guaranteed by characterization results.

6.3.6 Wakeup time from low-power mode

The wakeup times given in *Table 37* are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep mode: the wakeup event is WFE.
- WKUP1 (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 37. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ @V_{DD}, V_{DD} = V_{DDA}						Max	Unit
			2.0 V	2.4 V	2.7 V	3 V	3.3 V	3.6 V		
t_{WUSTOP}	Wakeup from Stop mode	Regulator in run mode	4.5	4.2	4.1	4.0	3.8	3.8	4.5	µs
		Regulator in low-power mode	8.2	7.0	6.4	6.0	5.7	5.5	9.0	
$t_{WUSTANDBY}$(1)	Wakeup from Standby mode	LSI and IWDG OFF	72.8	63.4	59.2	56.1	53.1	51.3	103	
$t_{WUSLEEP}$	Wakeup from Sleep mode		6						-	CPU clock cycles

1. Guaranteed by characterization results.

Table 38. Wakeup time using USART(1)

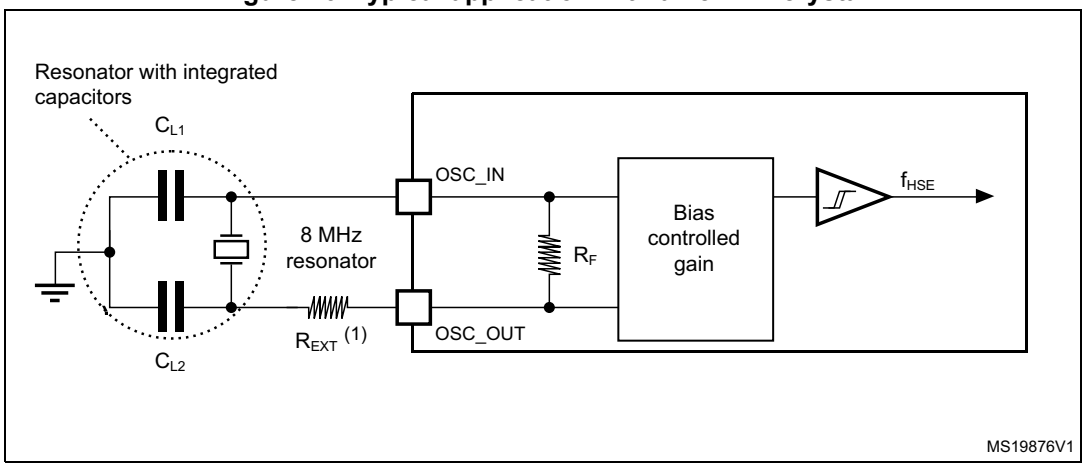
Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUUSART}$	Wakeup time needed to calculate the maximum USART baud rate allowing to wakeup up from Stop mode when the USART clock source is HSI	Stop mode with main regulator in low-power mode	-	13.125	µs
		Stop mode with main regulator in run mode	-	3.125	

1. Guaranteed by design.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 16*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 16. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 51. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	2 level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence or oscillator frequency deviation).

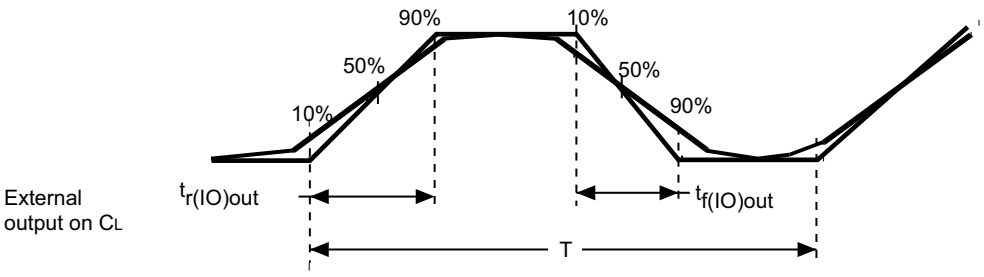
The test results are given in *Table 52*

Table 52. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	-0	NA	mA
	Injected current on PC0 pin (TTa pin)	-0	+5	
	Injected current PC0, PC1, PC2, PC3, PA0, PA1, PA2, PA3, PA4, PA6, PA7, PC4, PB0, PB10, PB11, PB13 with induced leakage current on other pins from this group less than -100 µA or more than +100 µA	-5	+5	
	Injected current on any other TT, FT and FTf pins	-5	NA	
	Injected current on all other TC, TTa and RESET pins	-5	+5	

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Figure 23. I/O AC characteristics definition



Maximum frequency is achieved if $(t_r + t_f) \leq 2/3)T$ and if the duty cycle is (45-55%)
when loaded by C_L (see note 1).

MS34942V1

1. See *Table 55: I/O AC characteristics*.

6.3.15 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 53*).

Unless otherwise specified, the parameters given in *Table 56* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 56. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST Input low level voltage	-	-	-	$0.3V_{DD}$+ 0.07(1)	V
$V_{IH(NRST)}$(1)	NRST Input high level voltage	-	$0.445V_{DD}$+ 0.398(1)	-	-	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	25	40	55	kΩ
$V_{F(NRST)}$(1)	NRST Input filtered pulse	-	-	-	100(1)	ns
$V_{NF(NRST)}$(1)	NRST Input not filtered pulse	-	500(1)	-	-	ns

1. Guaranteed by design.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

USB characteristics

Table 63. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design.

Table 64. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)		3.0(3)	3.6	V
V_{DI}(4)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(4)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(4)	Single ended receiver threshold		1.3	2.0	
Output levels					
V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F3xxx USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design.
5. R_L is the load connected on the USB drivers.

Figure 30. USB timings: definition of data signal rise and fall time

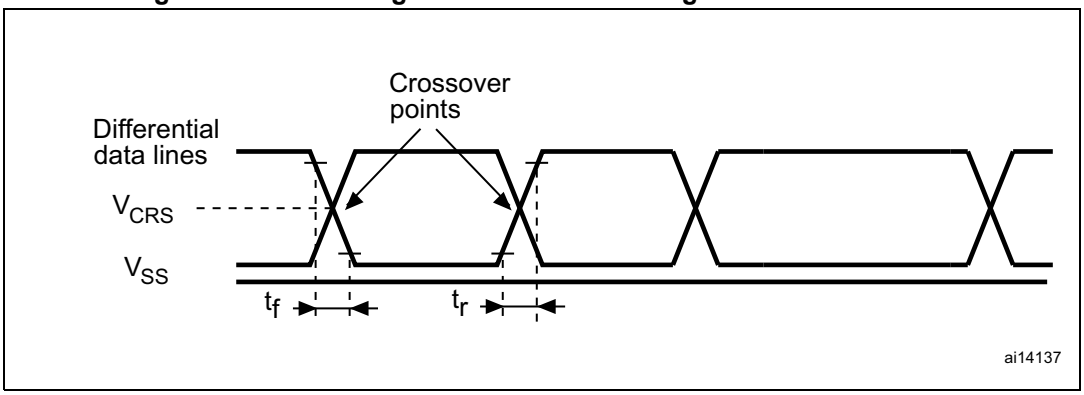


Table 65. USB: Full-speed electrical characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
t_r	Rise time(2)	C_L = 50 pF	4	-	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	-	20	ns

Table 66. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{ADC}(1)	Internal sample and hold capacitor	-	-	5	-	pF
t_{CAL}(1)	Calibration time	f_{ADC} = 72 MHz	1.56			µs
		-	112			$1/f_{ADC}$
t_{latr}(1)	Trigger conversion latency Regular and injected channels without conversion abort	CKMODE = 00	1.5	2	2.5	$1/f_{ADC}$
		CKMODE = 01	-	-	2	$1/f_{ADC}$
		CKMODE = 10	-	-	2.25	$1/f_{ADC}$
		CKMODE = 11	-	-	2.125	$1/f_{ADC}$
$t_{latrinj}$(1)	Trigger conversion latency Injected channels aborting a regular conversion	CKMODE = 00	2.5	3	3.5	$1/f_{ADC}$
		CKMODE = 01	-	-	3	$1/f_{ADC}$
		CKMODE = 10	-	-	3.25	$1/f_{ADC}$
		CKMODE = 11	-	-	3.125	$1/f_{ADC}$
t_S(1)	Sampling time	f_{ADC} = 72 MHz	0.021	-	8.35	µs
		-	1.5	-	601.5	$1/f_{ADC}$
TADCVREG_STUP(1)	ADC Voltage Regulator Start-up time	-	-	-	10	µs
t_{STAB}(1)	Power-up time	-	1			conversion cycle
t_{CONV}(1)	Total conversion time (including sampling time)	f_{ADC} = 72 MHz Resolution = 12 bits	0.19	-	8.52	µs
		Resolution = 12 bits	14 to 614 (t_S for sampling + 12.5 for successive approximation)			$1/f_{ADC}$
CMIR(1)	Common mode input signal	ADC differential mode	$(V_{SSA} + V_{REF+})/2$ - 0.18	$(V_{SSA} + V_{REF+})/2$	$(V_{SSA} + V_{REF+})/2$ + 0.18	V

1. Data guaranteed by design.

Figure 36. OPAMP Voltage Noise versus Frequency

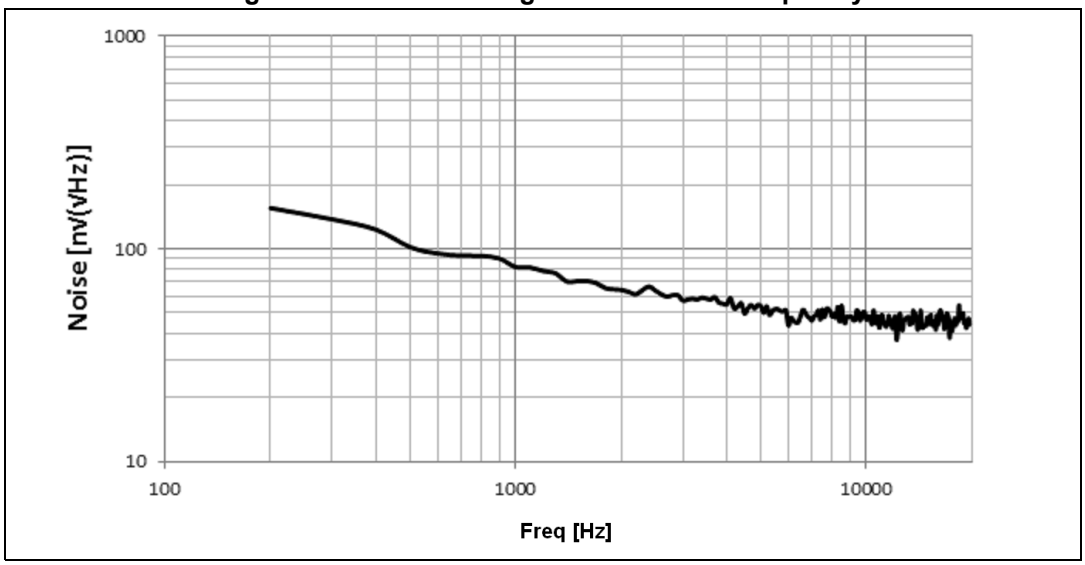


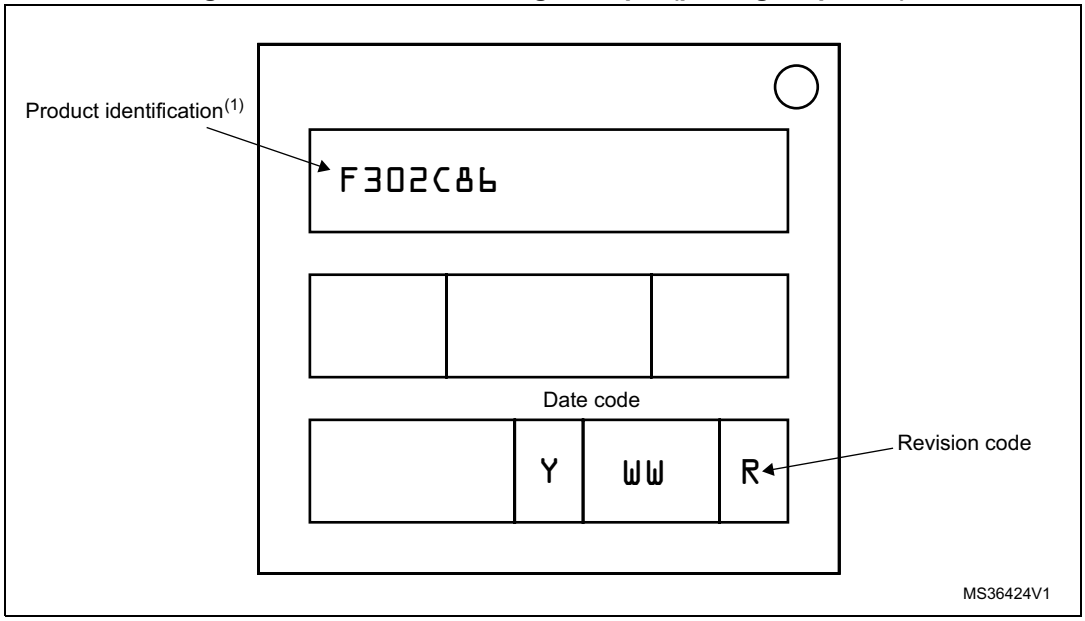
Table 78. WLCSP49 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values
Pitch	0.4
Dpad	260 µm max. (circular)
	220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed.

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

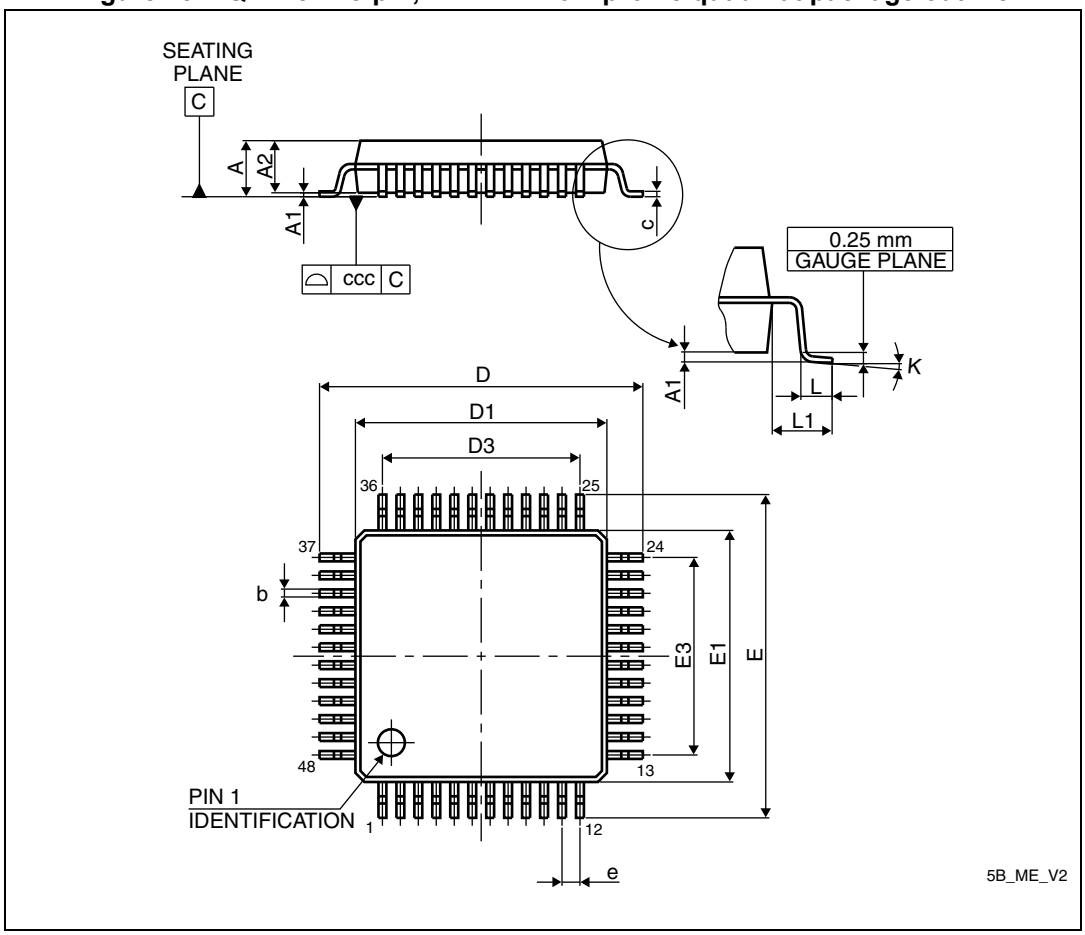
Figure 39. WLCSP49 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 80. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.